



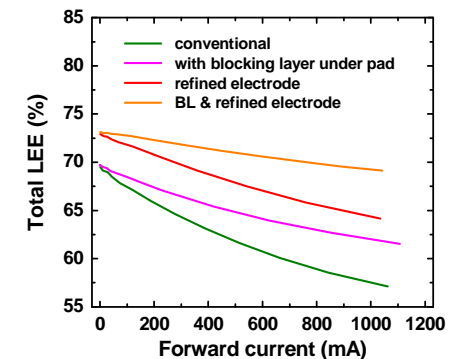
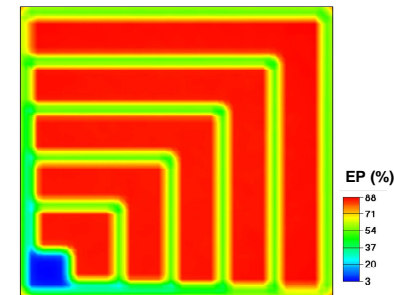
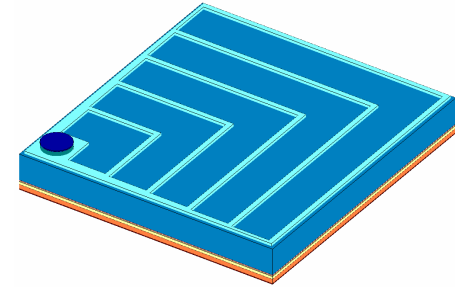
# Current crowding effect on light extraction efficiency of thin-film LEDs

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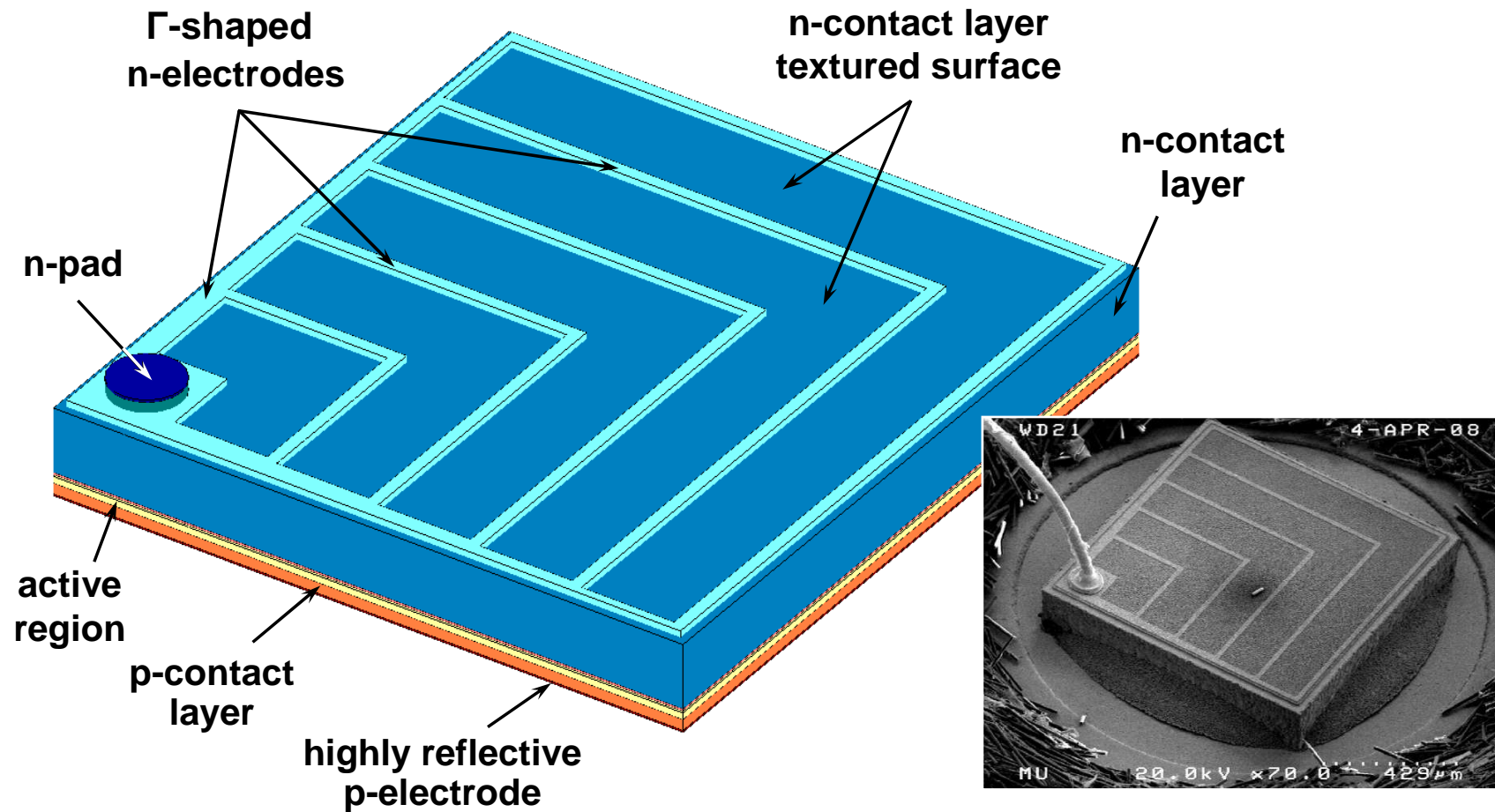
- current crowding and operation of thin-film high-power blue LED
- effect of the current crowding on light extraction efficiency — a new mechanism contributing to LED efficiency droop
- possible ways to improve the light extraction efficiency



# Basic design of $815 \times 875 \mu\text{m}^2$ blue LED die



V. Härle et al., Proc. SPIE 4996 (2003) 133 / phys. stat. solidi (a) 201 (2004) 2736



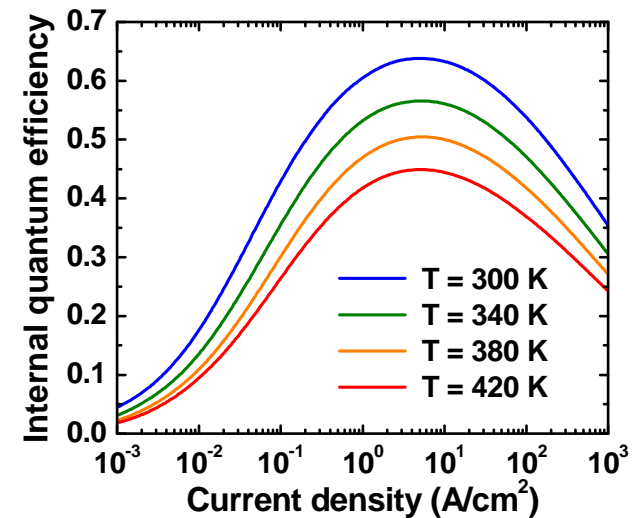
Micrograph of the die by MuAnalysis, Inc., 2008



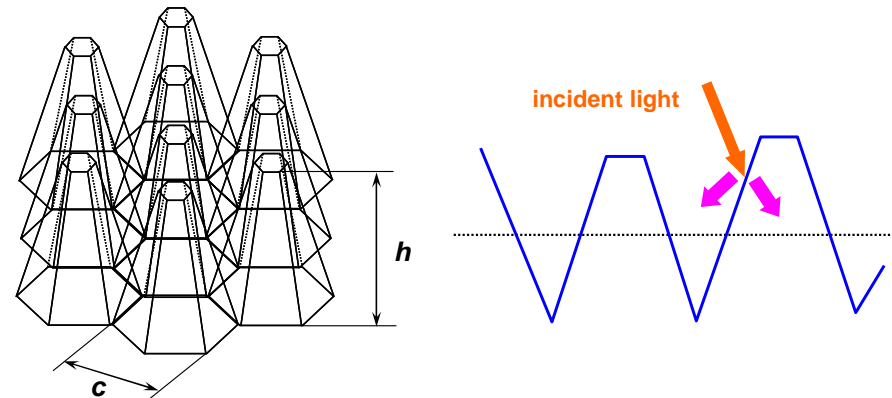
## Key elements of simulation model

SimuLED™ package is used for modeling:  
<http://www.str-soft.com/products/SimuLED>

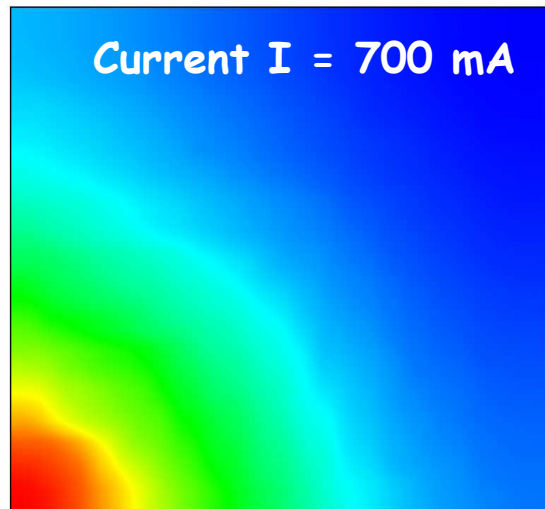
- 3D coupled simulation of electrical, thermal, and optical processes in the LED die
- Auger recombination is considered is the main non-thermal mechanism of the IQE droop at high current densities
- textured surface is modeled by closely packed hexagonal pyramids with the aspect ratio  $h/c \sim 4$
- optical properties of Au and Ag are used for n- and high-reflective p-electrodes, respectively



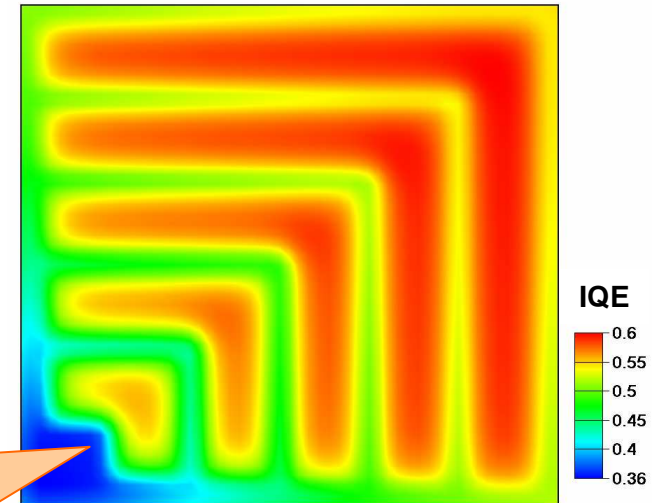
no electron leakage is predicted for InGaN MQW LED structure



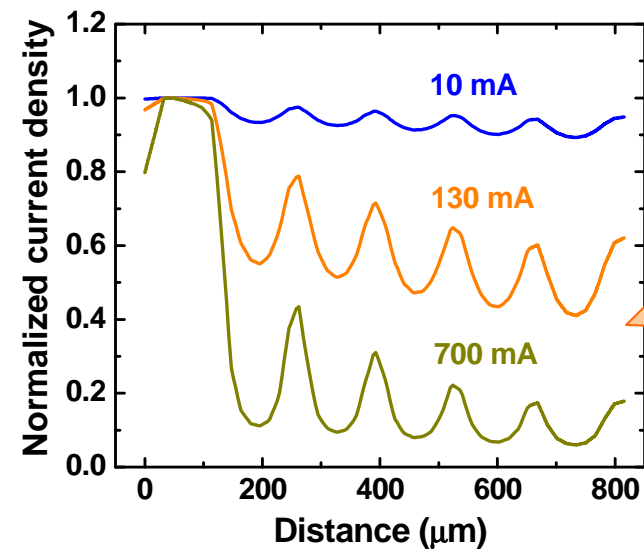
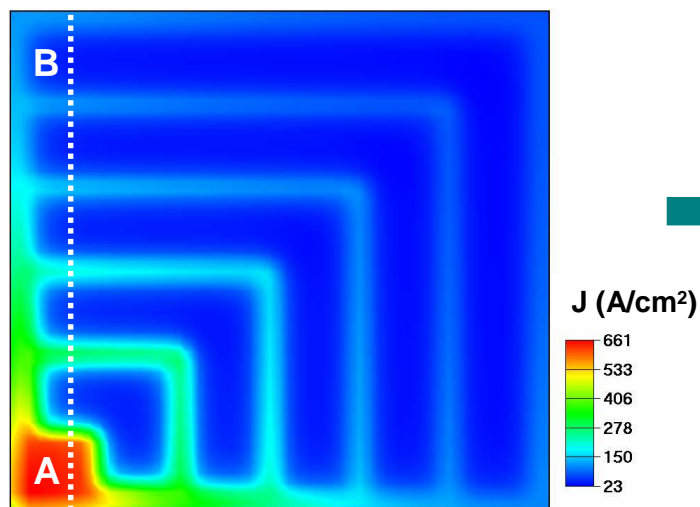
# Current crowding near/under n-electrodes



temperature,  
current density,  
and IQE  
distributions in  
the active region



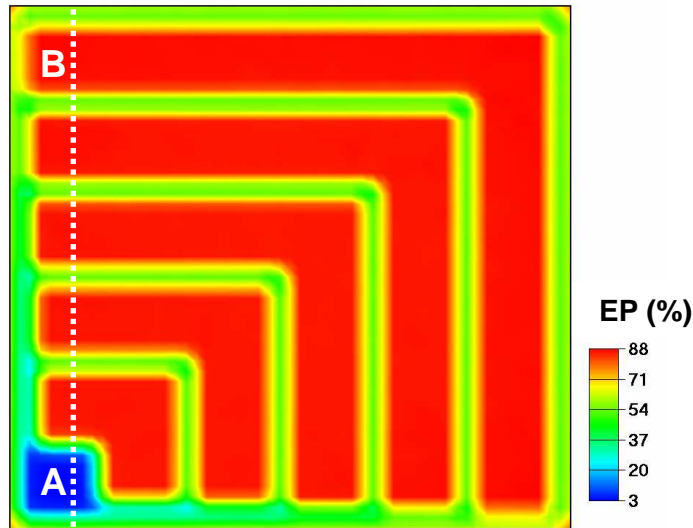
local IQE  
reduction in high-  
current density  
area



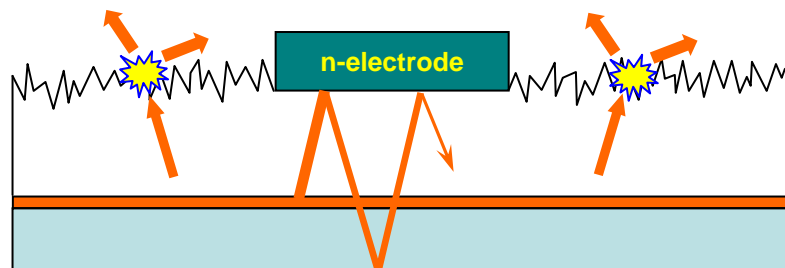
AB cross-  
section

current  
density non-  
uniformity  
depends on  
the total  
operating  
current

# Light extraction from the LED

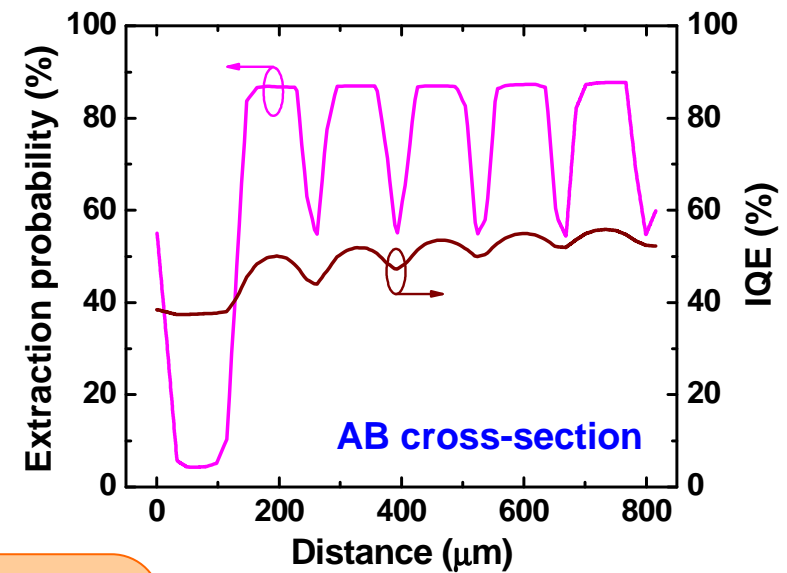


probability of light extraction falls down under and next to n-electrode



distribution of extraction probability is nearly independent of current

Current  $I = 700$  mA



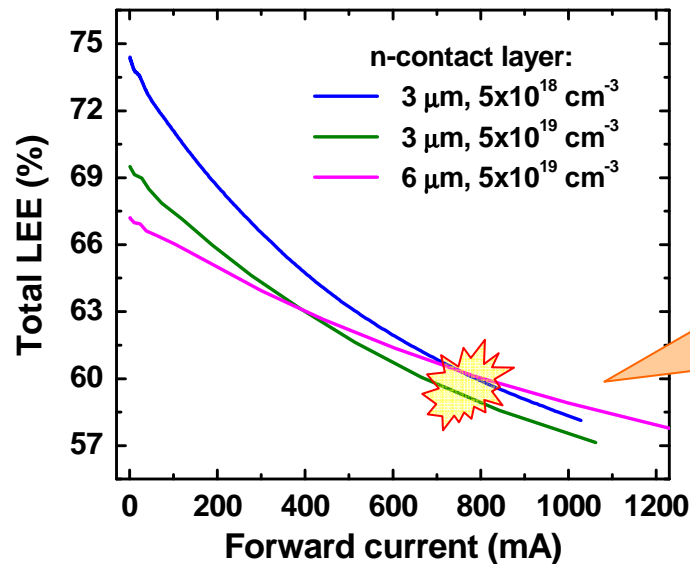
light generated under n-pad is not practically extracted from the die because of incomplete multiple reflection from metallic electrode



# Dependence of light extraction efficiency on current

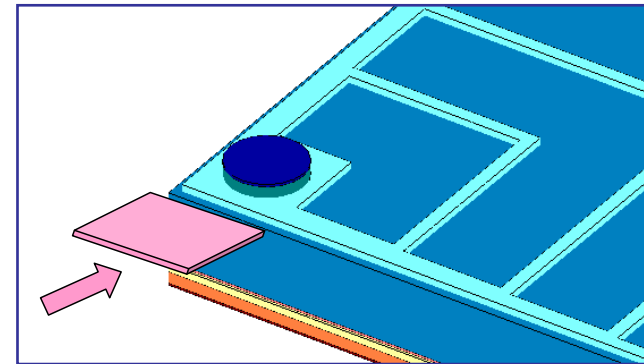
variation of n-contact layer parameters affects weakly the current crowding and, hence, the LEE at ~700-800 mA

alternative approaches are required

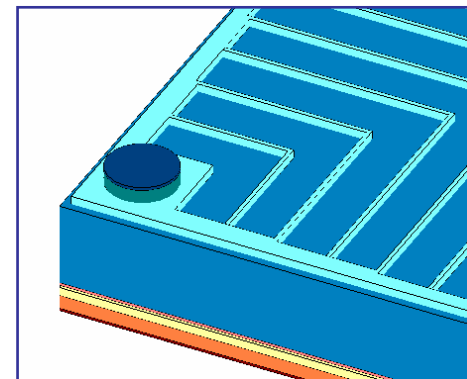


strong dependence of LEE on forward current

Approach 1: insertion of an insulating layer under the n-pad to avoid parasitic current flow in this region



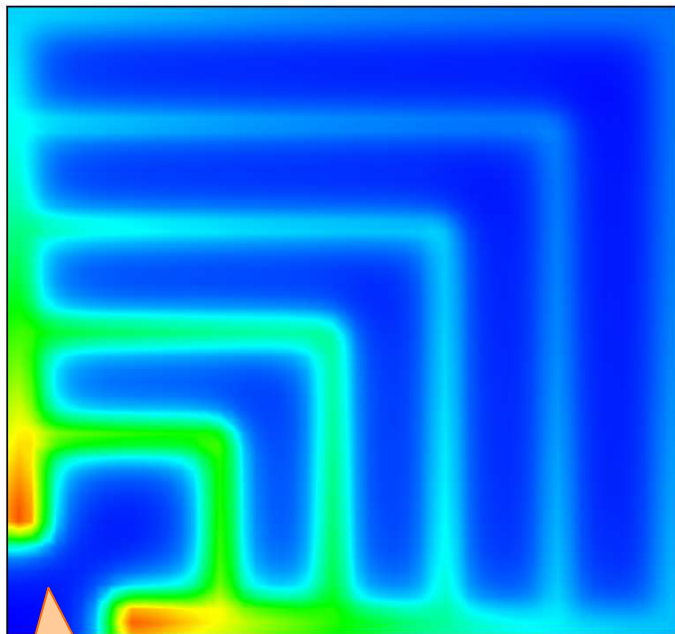
Approach 2: use of narrower Γ-shaped electrodes with reduced spacing between them



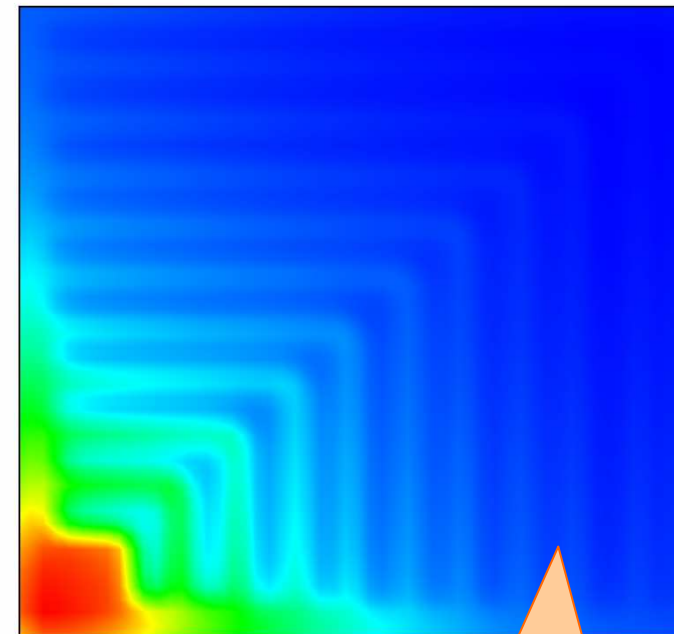
# Current spreading in LED dice of modified designs



Total current through the diode  $I = 700 \text{ mA}$



parasitic current  
flow under the n-pad  
is partly suppressed



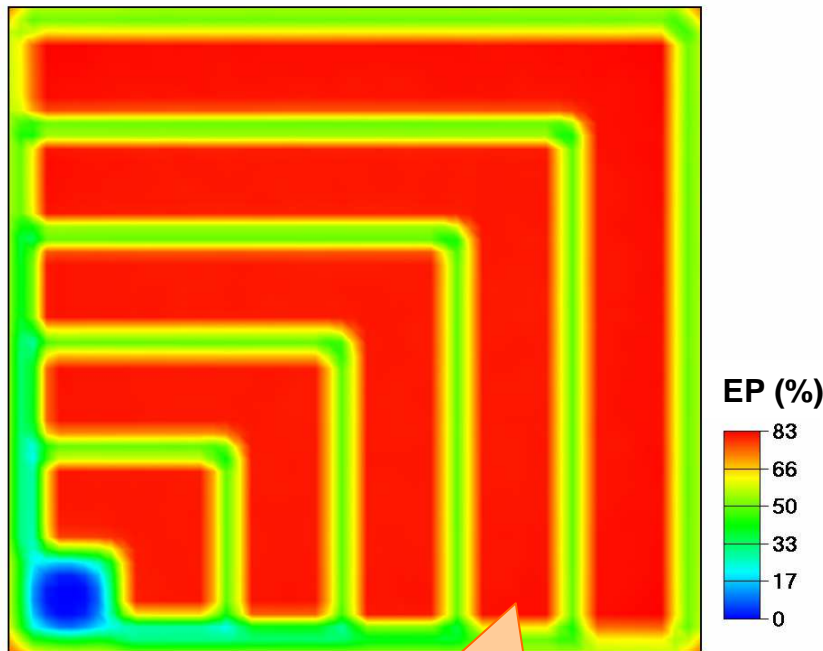
reduction of the  
current density  
contrast in the  
active region

both approaches are found  
to work well

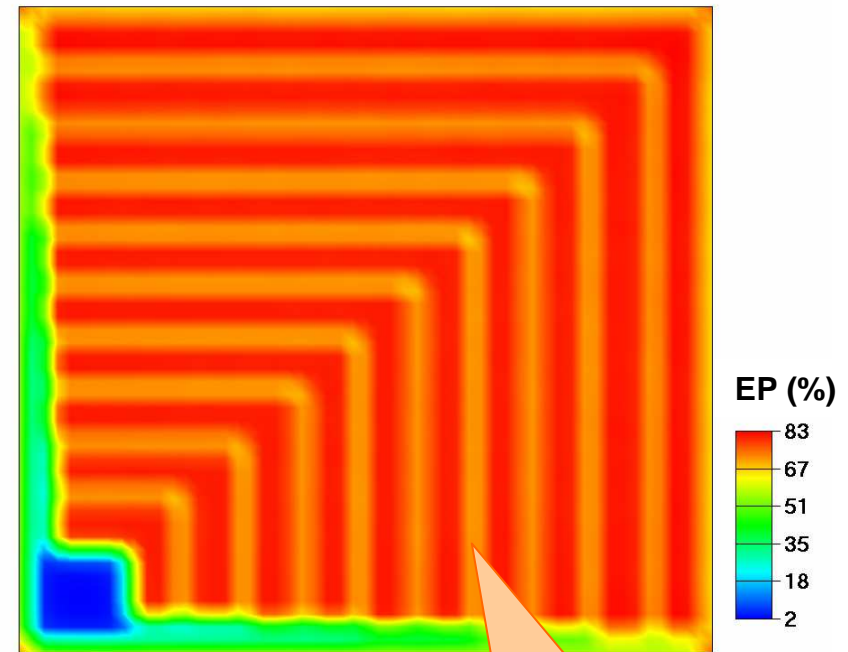
## Probability of light extraction from the dice of modified designs



Total current through the diode  $I = 700 \text{ mA}$



probability of light extraction is comparable with that of the basic die design



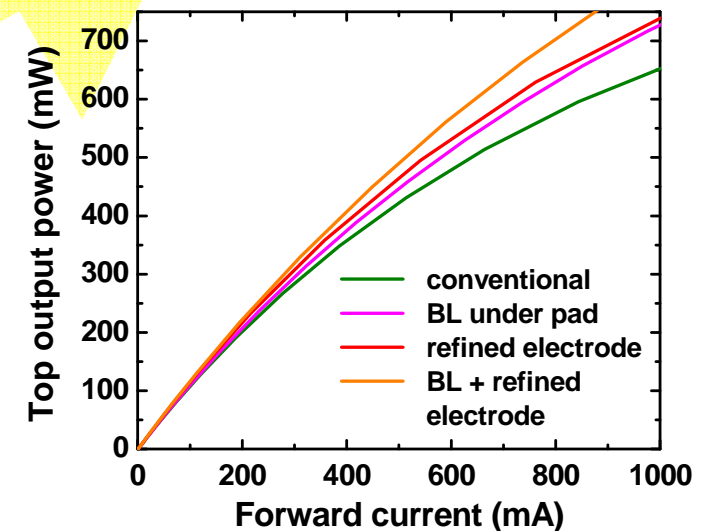
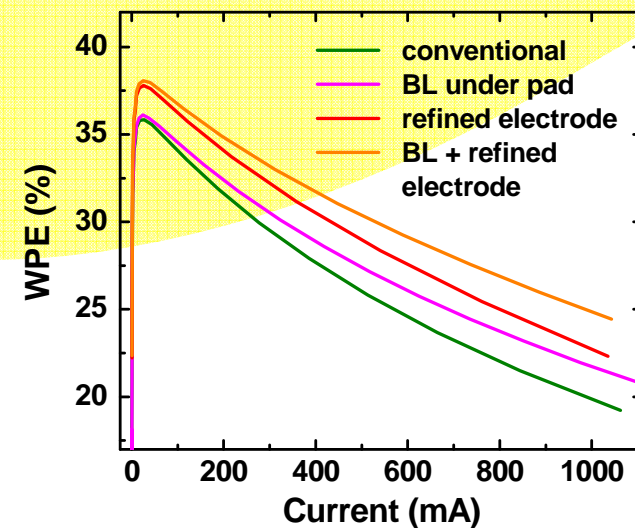
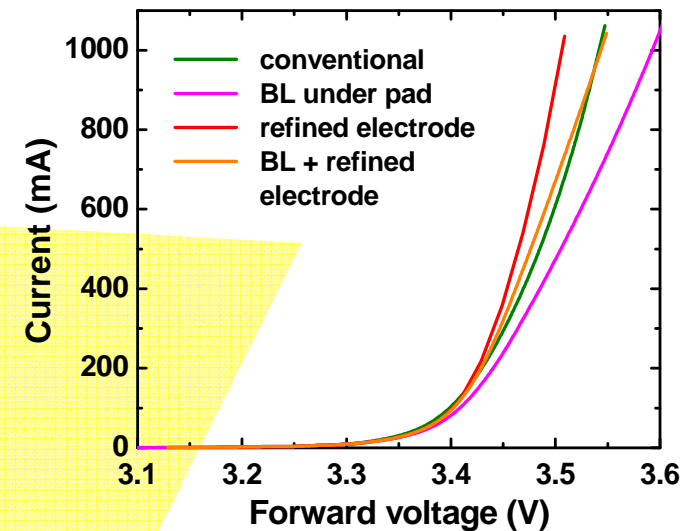
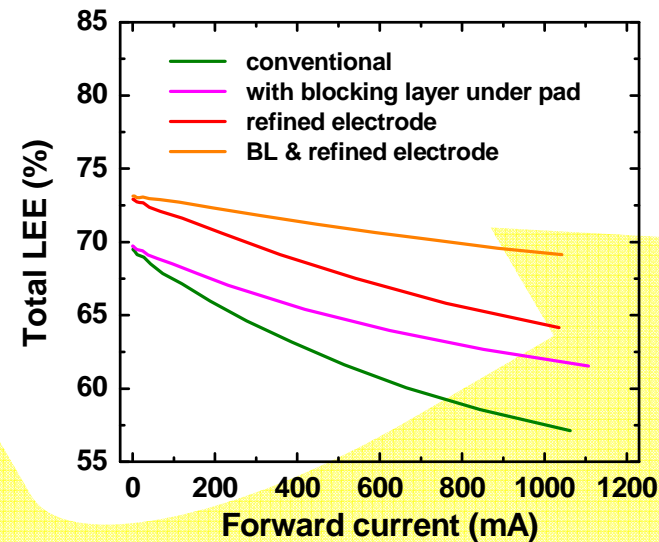
considerable enlarging of the area with high probability of light extraction

# Assessment of performance improvement due to variation of LED die design



Performance improvements at the current of 700 mA:

- LEE  $\uparrow$  from 60 to 70%
- $V_f$  remains the same
- optical power  $\uparrow$  from 530 to 635 mW (by ~20%)
- WPE  $\uparrow$  from 23 to 28% (by ~22%)





- ✓ current crowding may result in a strong dependence of light extraction efficiency (LEE) on operating current in vertical thin-film LEDs because of incomplete emitted light reflection from metallic n-electrodes
- ✓ predicted decay of LEE with current enhances the droop of total LED efficiency; this actually represent one more non-thermal mechanism limiting the LED performance
- ✓ the undesirable LEE dependence on current may be remarkably suppressed by appropriate modifications of the chip design; in particular, inserting of insulating film under the n-pad and the use of narrow electrodes with reduced spacing are found to be promising for improvement of LED performance